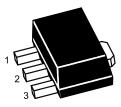
NPN Silicon Epitaxial Planar Power Transistor

Features

- Low saturation voltage
- High speed switching time
- High saturation current capability



1.Base 2.Collector 3.Emitter SOT-89 Plastic Package

Applications

· For power switching and power amplifier applications

Absolute Maximum Ratings (T_a = 25°C)

Parameter	Symbol	Value	Unit
Collector Base Voltage	V _{CBO}	80	V
Collector Emitter Voltage	VCEO	50	V
Emitter Base Voltage	Vebo	6	V
Collector Current	lc	3	А
Base Current	lв	0.6	А
Total Power Dissipation	P _{tot}	0.5 ¹⁾ 1 ²⁾	W
Junction Temperature	Tj	150	°C
Storage Temperature Range	T _{stg}	- 55 to + 150	°C

Thermal Characteristics

Parameter	Symbol	Max.	Unit	
Thermal Resistance from Junction to Ambient	Reja	250 ¹⁾ 125 ²⁾	°C/W	

¹⁾Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.

²⁾Device mounted on FR-4 substrate PC board, 2oz copper, with 1-inch square copper plate in still air.



Characteristics at T_a = 25°C

Parameter	Symbol	Min.	Тур.	Max.	Unit
DC Current Gain at V_{CE} = 2 V, I _C = 100 mA at V_{CE} = 2 V, I _C = 2 A	hfe hfe	120 40	-	400 -	-
Collector Base Cutoff Current at V_{CB} = 80 V	Ісво	-	-	0.1	μA
Emitter Base Cutoff Current at $V_{EB} = 6 V$	Іево	-	-	0.1	μA
Collector Base Breakdown Voltage at I_c = 0.1 mA	V _{(BR)CBO}	80	-	-	V
Collector Emitter Breakdown Voltage at I_c = 10 mA	V _{(BR)CEO}	50	-	-	V
Emitter Base Breakdown Voltage at I _E = 0.1 mA	V _{(BR)EBO}	6	-	-	V
Collector Emitter Saturation Voltage at I_c = 1.5 A, I_B = 75 mA	V _{CE(sat)}	-	-	0.5	V
Base Emitter Saturation Voltage at I _c = 1.5 A, I _B = 75 mA	V _{BE(sat)}	-	-	1.2	V
Transition Frequency at V_{CE} = 2 V, I _C = 100 m A	fT	-	100	-	MHz
Collector Output Capacitance at $V_{CB} = 10 \text{ V}, f = 1 \text{ MHz}$	Cob	-	10	-	pF
Turn-on Time at V _{CC} = 30 V, I _C = 1.5 A, I _{B1} = -I _{B2} = 75 mA	t _{on}	-	100	-	ns
Storage Time at V _{CC} = 30 V, I _C = 1.5 A, I _{B1} = -I _{B2} = 75 mA	t _{stg}	-	500	-	ns
Fall Time at V _{CC} = 30 V, I _C = 1.5 A, I _{B1} = -I _{B2} = 75 mA	tr	-	100	-	ns



Electrical Characteristics Curves

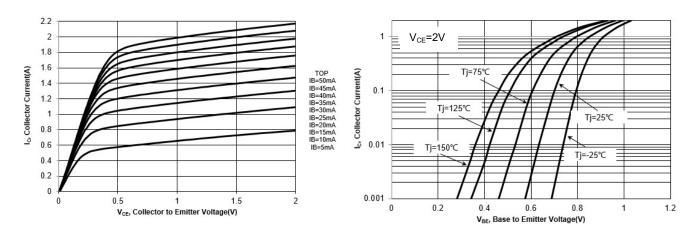
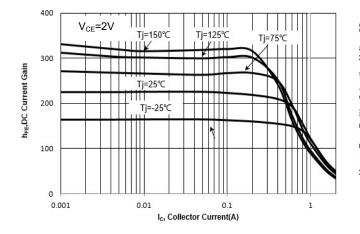


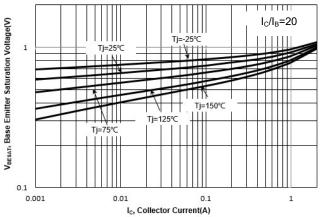
Fig. 1 Output Characteristics Curve

Fig. 2 Collector Curren vs. V_{BE}

Fig. 3 hFE vs. Collector Current

Fig. 4 V_{BE(sat)} vs. Collector Current







Electrical Characteristics Curves

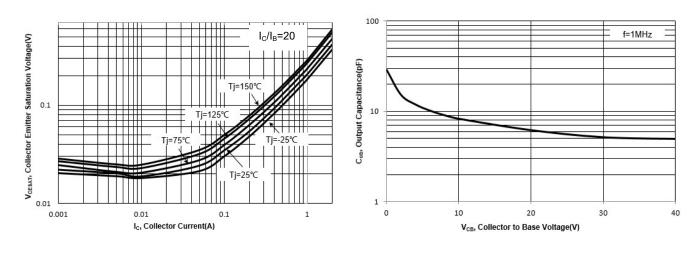
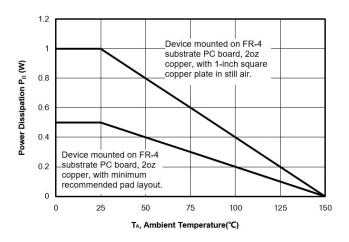


Fig. 5 V_{CE(sat)} vs. Collector Current

Fig 6. Output Capacitance

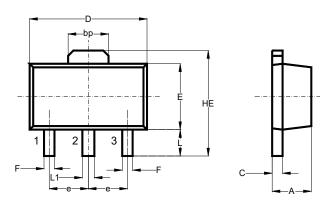
Fig. 7 Power Derating Curve

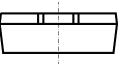




Package Outline (Dimensions in mm)

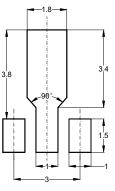






Unit	А	bp	С	D	E	F	HE	е	L	L1
	1.6	1.60	0.5	4.6	2.6	0.45	4.25	1.5	1.05	0.51
mm	1.4	1.50	0.3	4.4	2.4	0.35	3.75	typ.	0.95	0.41

Recommended Soldering Footprint



Packing information

	Tape Width (mm)	Pitch		Reel Size		
Package		mm	inch	mm	inch	Per Reel Packing Quantity
007.00	10	0.04	0.045 - 0.004	178	7	1,000
SOT-89	12	8 ± 0.1	0.315 ± 0.004	330	13	4,000

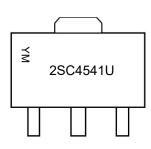
Marking information

" 2SC4541U " = Part No. "YM" = Date Code Marking

"Y" = Year

"M" = Month

Font type: Arial



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